

MDB6S, MDB8S, MDB10S

Single-Phase Bridge Rectifiers

1 A, MicroDIP

Description

With the ever pressing need to improve power supply efficiency and reliability, the MDBxS family is focused on offering a best in class small form factor combined with best in class efficient rectifier performance.

The “S” family offers industry leading balance of efficiency, size, and cost. They offer designers improved efficiency by achieving an industry leading V_F of 0.935 V Typ. at 1 A 25°C, and a V_F of 1.165 V Typ. at 5 A 25°C. These lower V_F values offer roughly a 5% efficiency improvement over measured competitive same form factor devices. This lower V_F vs. competitive devices results in cooler and more efficient power supply operation.

The design supports a 30 A I_{FSM} rating to absorb high surge currents and offers rated breakdown voltages up to 1000 V.

Finally, the MDBxS family achieves all this in a small form factor micro-dip package – offering a max height of 1.6 mm, and requiring only 35 mm² of board space.

Features

- Low Package Profile: 1.60 mm (max)
- Small Area Requirements: 35 mm²
- Efficient V_F
 - ◆ 0.935 V (Typ) at 1 A
 - ◆ 1.165 V (Typ) at 5 A
- $I_F(AV) = 1.0$ A
- $I_{FSM} = 30$ A
- Glass Passivated Junctions
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant
- UL Certification: E352360

ORDERING INFORMATION

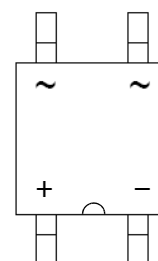
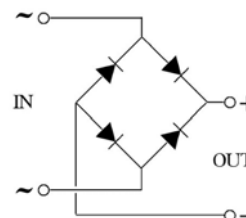
Part Number	Top Mark	Package	Packing Method [†]
MDB6S	MDB6S	MicroDIP	Tape and Reel
MDB8S	MDB8S		
MDB10S	MDB10S		

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



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MicroDIP
CASE 948BS

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Table 1. ABSOLUTE MAXIMUM RATINGS Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value			Unit
		MDB6S	MDB8S	MDB10S	
V_{RRM}	Maximum Repetitive Peak Reverse Voltage	600	800	1000	V
V_{RMS}	Maximum RMS Voltage	420	560	700	V
V_{DC}	Maximum DC Blocking Voltage	600	800	1000	V
$I_{F(AV)}$	Average Rectified Forward Current (Note 1)	1.0			A
I_{FSM}	Peak Forward Surge Current (Note 2)	30			A
I^2t	I^2t Rating for fusing ($t < 8.3$ ms)	3.735			A ² S
T_J	Operating Junction Temperature Range	-55 to +150			$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to +150			$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 60 Hz sine wave, R-load, $T_A = 25^\circ\text{C}$ on FR-4 PCB.
- 60 Hz sine wave, Non-repetitive 1 cycle peak value, $T_J = 25^\circ\text{C}$.

Table 2. THERMAL CHARACTERISTICS (Note 3)

Symbol	Parameter		Typ	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	Measurement with Dual Die	250	$^\circ\text{C}/\text{W}$
		Measurement with Single Die	150	$^\circ\text{C}/\text{W}$
Ψ_{JL}	Thermal Characterization, Junction-to-Lead	Measured at Anode pin	57	$^\circ\text{C}/\text{W}$
		Measured at Cathode pin	15	$^\circ\text{C}/\text{W}$

- Device mounted on FR-4 PCB with board size = 76.2 mm x 114.3 mm (JESD51-3 standards).

Table 3. ELECTRICAL CHARACTERISTICS Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_F	Maximum Forward Voltage	$I_F = 1$ A, Pulse measurement, Per diode			1.1	V
I_R	Maximum Reverse Current	At V_{RRM} , Pulse measurement, Per diode			10	μA
C_J	Typical Junction Capacitance	$V_R = 4$ V, $f = 1$ MHz		10		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL PERFORMANCE CHARACTERISTICS

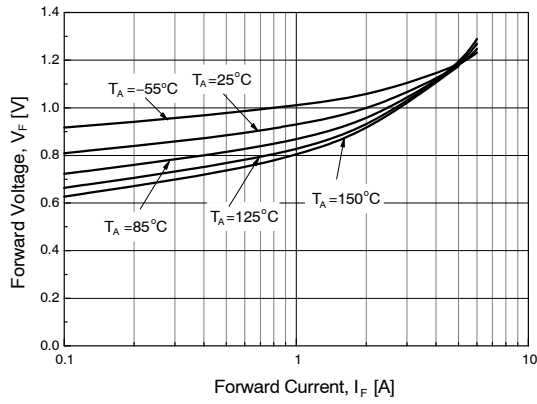


Figure 1. Forward Voltage vs. Forward Current

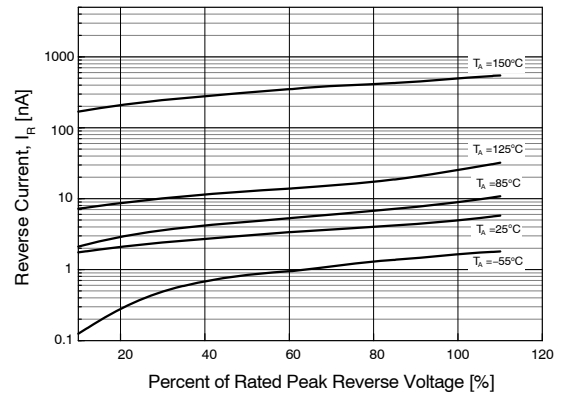


Figure 2. Typical Reverse Current Characteristics

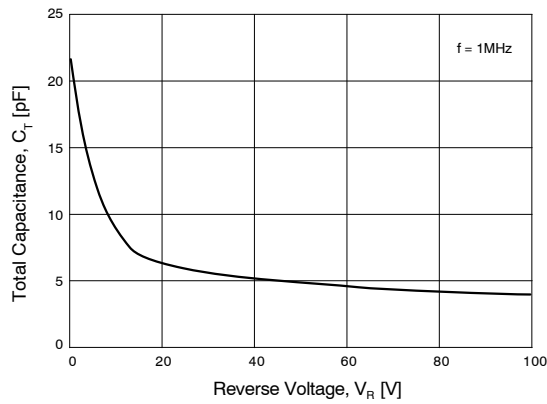
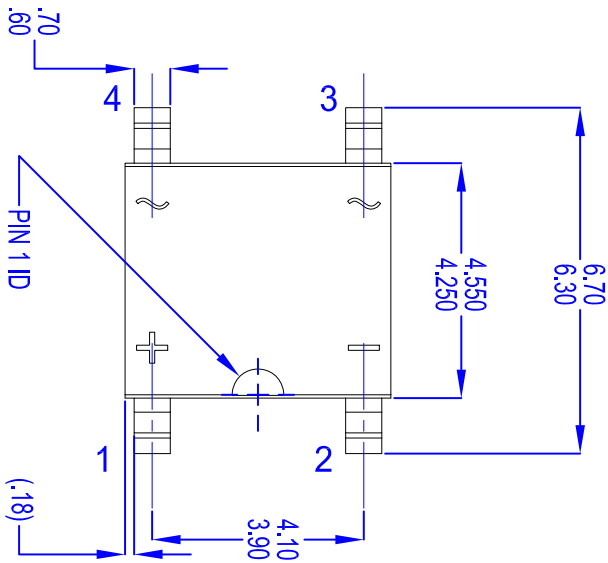


Figure 3. Total Capacitance

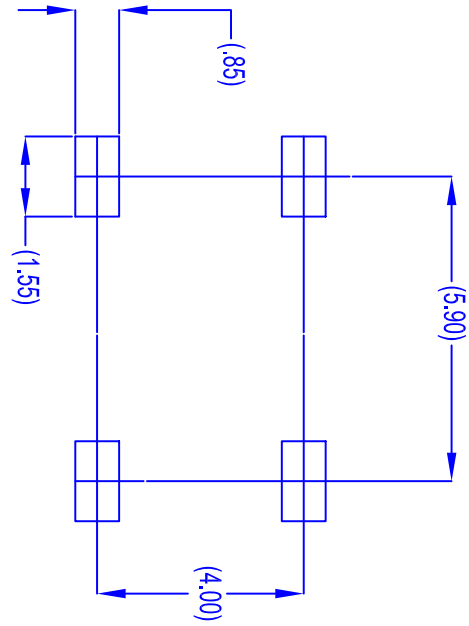
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PACKAGE DIMENSIONS

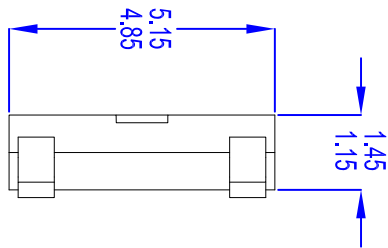
TSSOP4 5.0x4.4 / Micro-DIP
CASE 948BS
ISSUE O



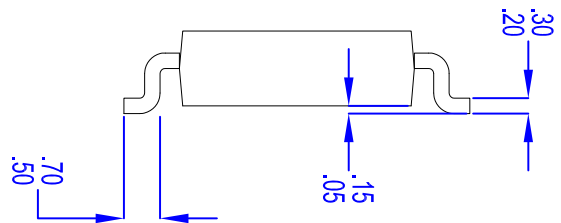
TOP VIEW



LAND PATTERN RECOMMENDATION



SIDE VIEW



END VIEW

NOTES:

- A. THIS PACKAGE DOES NOT CONFORM TO ANY REFERENCE STANDARD.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.

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